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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DO	ATTY DOCKET NO. 118215		APPLICATION NO. New US Application		
INFORMATION DISCLOSURE STATEMENT									
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10:-	1	JP A 6-308872 (with abstract and translation)	11/04/1994		Japan				
ver	2	JP A 2003-297974 (with abstract and translation)	10/17/2003		Japan				
m	3	JP A 2003-142666 (with abstract and translation)	05/16/2003		Japan				
NOV	4	JP A 2003-298006 (with abstract and translation)	10/17/2003		Japan				
12	5	JP A 2001-282423 (with abstract and translation)	10/12/2001		Japan				
W_	6	JP A 2001-282424 (with abstract and translation)	10/12/2001		Japan				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)									
50 :-	7 "A breakthrough technologyfor leading edge microelectronics manufacturing"., www.holtronic.ch,								
. 642%-									
EXAMINER OF THE CONSIDERED 5/16/05						6/05			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

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200	i	SHIMODA et al., "Surface Free Technology by Laser Annealing (SUFTLA)", IEEE, 1999, pp. 289-292.							
102	2	UTSUNOMIYA et al., "Low Temperature Poly-Si TFTs on Plastic Substrate Using Surface Free Technology by Laser Ablation/Annealing (SUFTLA™), SID 00 DIGEST, 2000, pp. 916-919.							
100	3	SHIMODA, "Future Trend of TFTs", As	ia D	isplay/IDV	V '01, pp. 327-330.				
52	4	UTSUNOMIYA et al., "Low Temperature Poly-Si TFT-LCD Transferred onto Plastic Substrate Using Surface Free Technology by Laser Ablation/Annealing (SUFTLA®)", Asia Display/IDW '01, pp. 339-342.							
101	5	SHIMODA, "Future Trend of TFT Techn	nolo	gy", AM-L	CD '02, pp. 5-8.				
	7					<u></u>			
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